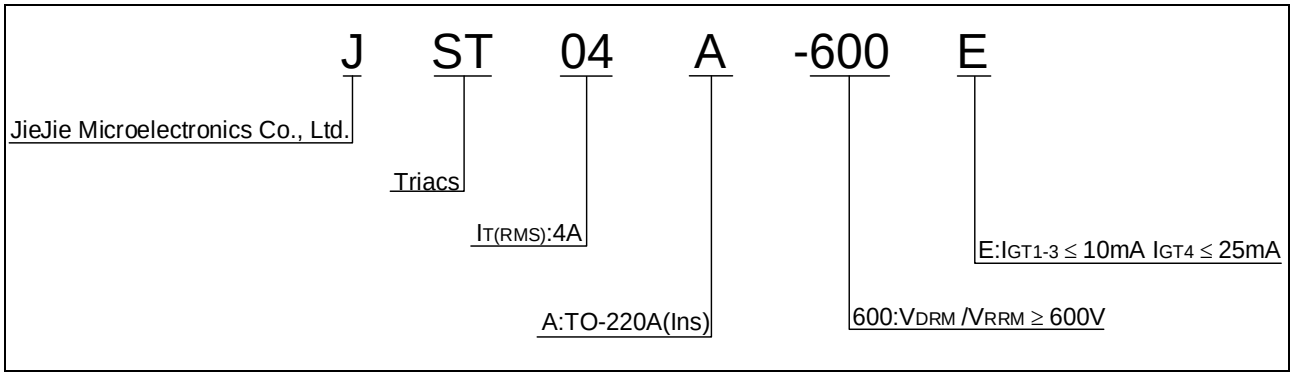
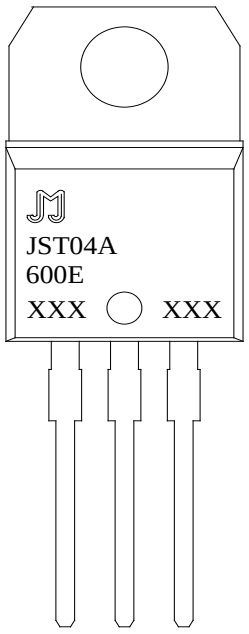
Peak gate power

ORDERING INFORMATION



MARKING



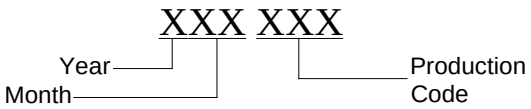


FIG.1: Maximum power dissipation versus RMS on-state current

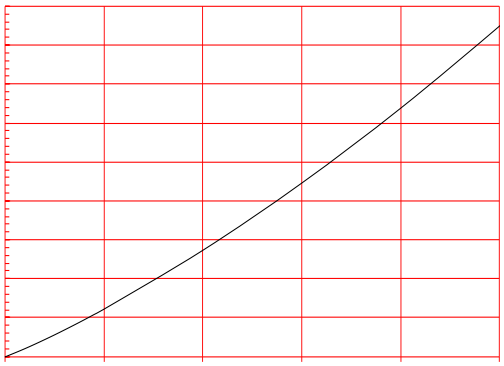


FIG.2: RMS on-state current versus case temperature

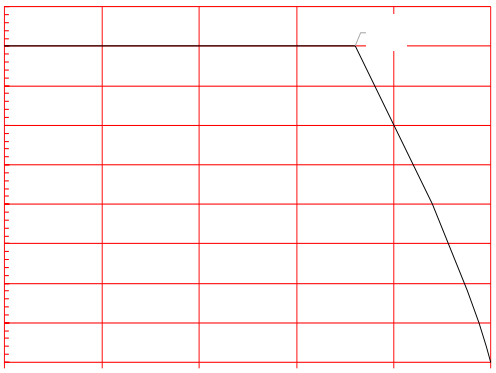


FIG.3: Surge peak on-state current versus number of cycles

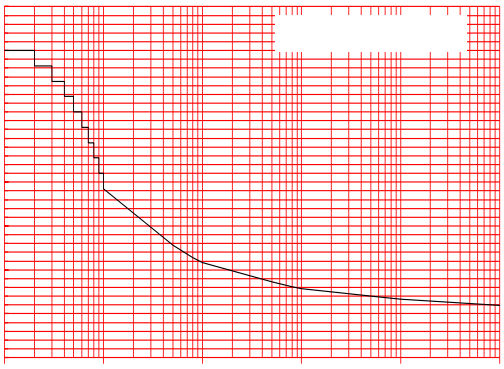


FIG.4: On-state characteristics

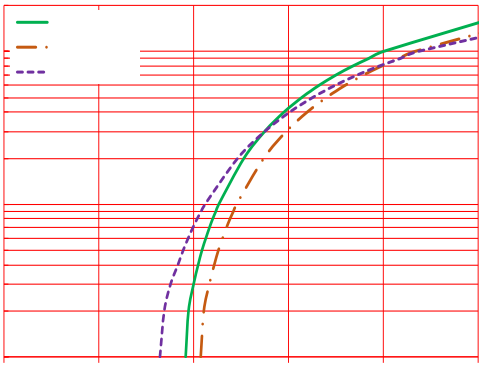


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t
(- - : dI/dt<80A/μs; : dI/dt<40A/μs)

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		- -				
JST04A-600E	600	10	25	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
May 18, 2023	A.1.0	Last updated

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